

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	700	V
Gate-Source Voltage	V_{GS}	± 30	V
Drain Current	$I_D(T_c=25)$	4.0	A
Drain Current	$I_D(T_c=100)$	2.5	A
Drain Current - Pulsed	I_{DM}	16	A
Single Pulsed Avalanche Energy	E_{AS}	260	mJ
Power Dissipation	P_{tot}	36	W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	
Junction-to-Case	$R_{\theta JC}$	3.47	/W
Junction-to-Ambient	$R_{\theta JA}$	62.5	/W

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	700			V
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_j$	$I_D=250\mu A$ Referenced to 25		0.65		V/
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}$ $I_D=250\mu A$	2.0		4.0	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=700V$ $V_{GS}=0V$ $T_j=25$			1	μA
		$V_{DS}=560V$ $V_{GS}=0V$ $T_j=125$			10	μA
Forward Transconductance	g_{FS}	$V_{DS}=40V$ $I_D=2.0A$		4.0		S
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 30V$			± 100	nA
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=2.0A$		1.93	2.2	Ω
Input Capacitance	C_{iss}	$V_{GS}=0V$ $V_{DS}=25V$ $V_F=1.0MHz$		520		pF
Turn-Off Delay Time	$t_{d(off)}$	$V_{DD}=350V$ $I_D=4.0A$ $R_G=25\Omega$		25		ns

/ Electrical Characteristics(Ta=25 °C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	Q_g	$I_D=4.0A$ $V_{DS}=560V$ $V_{GS}=10V$		17.4		nC
Gate-to-Source Charge	Q_{gs}			4.8		nC
Gate-to-Drain Charge	Q_{gd}			5.4		nC
Continuous Diode Forward Current	I_S				4.0	A
Diode Forward Voltage	V_{SD}	$I_S=4.0A$ $V_{GS}=0V$ $T_j=25$			1.4	V
Reverse Recovery Time	t_{rr}	$I_f=4.0A$ $T_j=25$ $di/dt=100A/\mu s$		250		nS
Reverse Recovery Charge	Q_{rr}			1.5		uC

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Repetitive rating: Pulse width limited by maximum junction temperature

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@58%/Y_{GG}@83Y/0@63 p K/U_J @58 °C/L_{DV}@713D

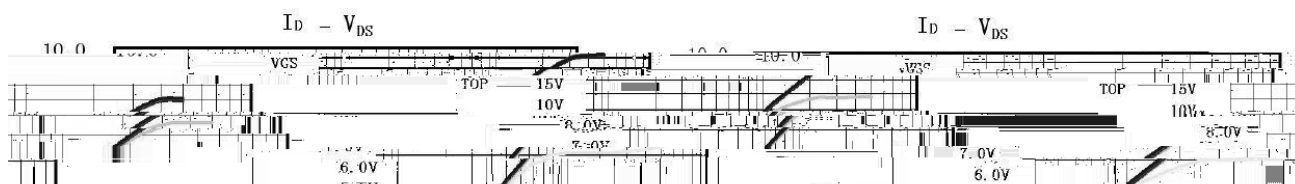
Starting $T_j=25^\circ C$, VDD=50V, L=30mH, RG=25Ω, I_{AS}=4.0A

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Pulse Test:Pulse width≤300μs,Duty cycle≤ 2%

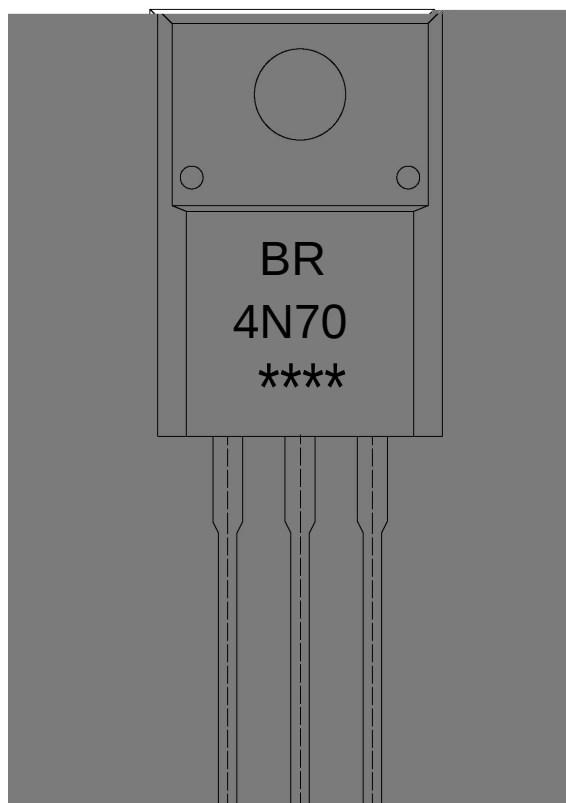
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

4N70

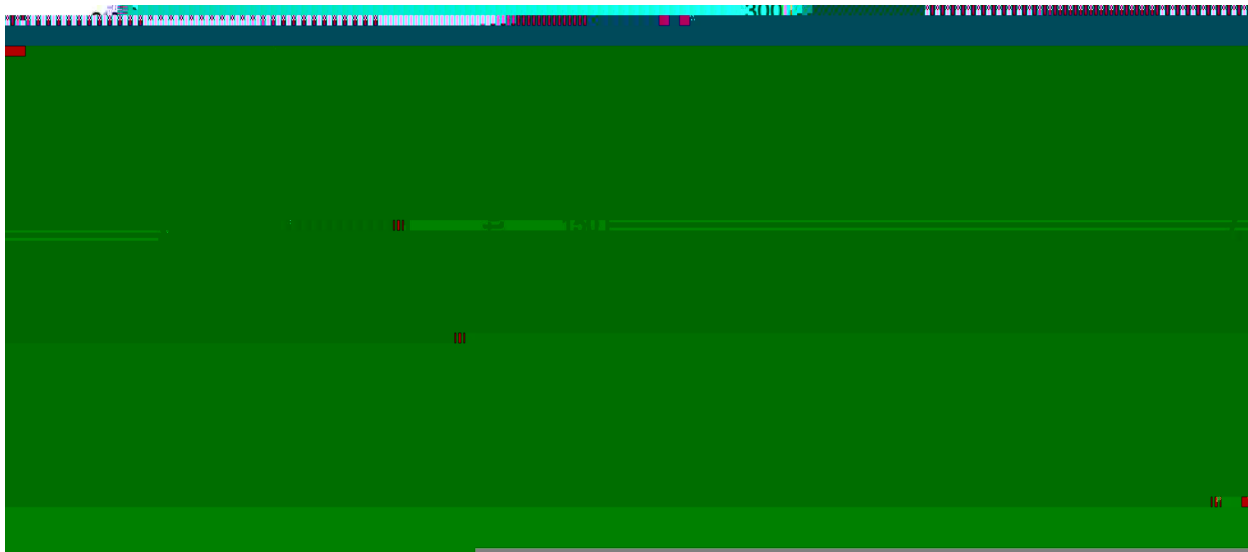
Note:

BR: Company Code

4N70: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

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|---|-----|--------------------|----|------------------------|---|
| 1 | 25 | 150 $\frac{3}{8}$ | 60 | 90sec; | 1.Preheating:25~150 $\frac{3}{8}$, Time:60~90sec. |
| 2 | 255 | $\pm 5\frac{3}{8}$ | 5 | ± 0.5 sec; | 2.Peak Temp.:255 $\pm 5\frac{3}{8}$, Duration:5 ± 0.5 sec. |
| 3 | | | 2 | 10 $\frac{3}{8}$ /sec. | 3. Cooling Speed: 2~10 $\frac{3}{8}$ /sec. |

/ Resistance to Soldering Heat Test Conditions

270 $\pm 5\frac{3}{8}$ 10 ± 1 sec. Temp.:270 ± 5 Time:10 ± 1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension		
	Units/Bag	Bags/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Bag	Inner Box	Outer Box